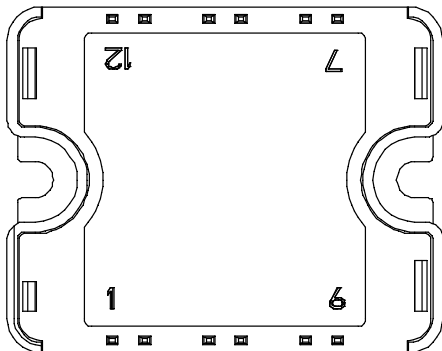
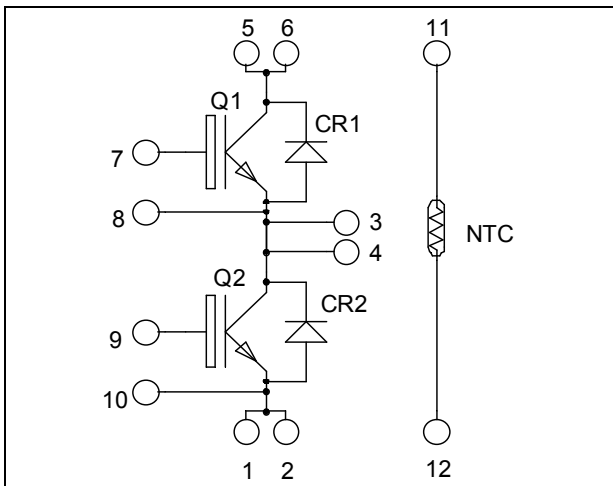


**Phase leg  
Trench + Field Stop IGBT®  
Power Module**

**$V_{CES} = 1700V$   
 $I_C = 30A @ T_c = 80^\circ C$**



Pins 1/2 ; 3/4 ; 5/6 must be shorted together

### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

### Features

- Trench + Field Stop IGBT® Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Very low stray inductance
  - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage	1700	V
$I_C$	Continuous Collector Current	$T_c = 25^\circ C$	45
		$T_c = 80^\circ C$	30
$I_{CM}$	Pulsed Collector Current	$T_c = 25^\circ C$	70
$V_{GE}$	Gate - Emitter Voltage	$\pm 20$	V
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	210
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^\circ C$	60A@1600V

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1700V$			250	$\mu\text{A}$
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15V$ $I_C = 30A$		2.0 2.4	2.4	V
		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$				
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1.5mA$	5.2	5.8	6.4	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			600	nA

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{ies}$	Input Capacitance	$V_{GE} = 0V, V_{CE} = 25V$		2500		pF
$C_{res}$	Reverse Transfer Capacitance	$f = 1MHz$		90		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $25^\circ\text{C}$ ) $V_{GE} = \pm 15V$ $V_{Bus} = 900V$ $I_C = 30A$ $R_G = 18\Omega$		100		ns
$T_r$	Rise Time			70		
$T_{d(off)}$	Turn-off Delay Time			650		
$T_f$	Fall Time			80		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $125^\circ\text{C}$ ) $V_{GE} = \pm 15V$ $V_{Bus} = 900V$ $I_C = 30A$ $R_G = 18\Omega$		100		ns
$T_r$	Rise Time			70		
$T_{d(off)}$	Turn-off Delay Time			750		
$T_f$	Fall Time			100		
$E_{on}$	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 900V$		17		mJ
$E_{off}$	Turn-off Switching Energy	$I_C = 30A$ $R_G = 18\Omega$		15		

**Reverse diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		1700			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 1700V$			250 500	$\mu\text{A}$
		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$				
$I_F$	DC Forward Current	$T_C = 80^\circ\text{C}$		50		A
$V_F$	Diode Forward Voltage	$I_F = 50A$ $V_{GE} = 0V$		1.8 1.9	2.2	V
		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$				
$t_{rr}$	Reverse Recovery Time	$I_F = 50A$ $V_R = 900V$ $di/dt = 800A/\mu\text{s}$		385 490		ns
			$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$			
$Q_{rr}$	Reverse Recovery Charge	$I_F = 50A$ $V_R = 900V$ $di/dt = 800A/\mu\text{s}$		14 23		$\mu\text{C}$
			$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$			
$E_r$	Reverse Recovery Energy	$I_F = 50A$ $V_R = 900V$ $di/dt = 800A/\mu\text{s}$		6 12		mJ
			$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$			

## Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
R <sub>thJC</sub>	Junction to Case Thermal Resistance	IGBT		0.60	°C/W	
		Diode		0.70		
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, I isol<1mA, 50/60Hz	3500			V	
T <sub>J</sub>	Operating junction temperature range	-40		150	°C	
T <sub>STG</sub>	Storage Temperature Range	-40		125		
T <sub>C</sub>	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2.5	4.7	N.m
Wt	Package Weight				80	g

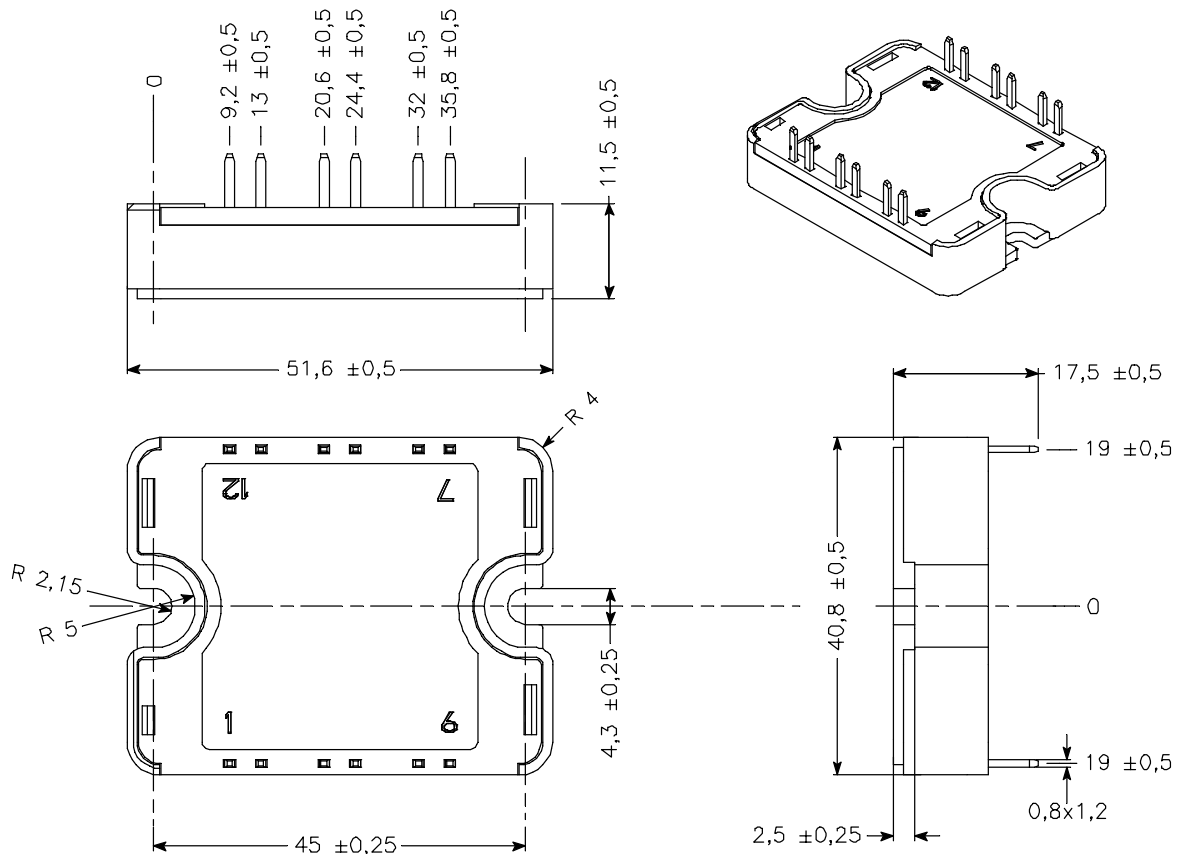
## Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
B <sub>25/85</sub>	T <sub>25</sub> = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T} - \frac{1}{T_{25}}\right)\right]}$$

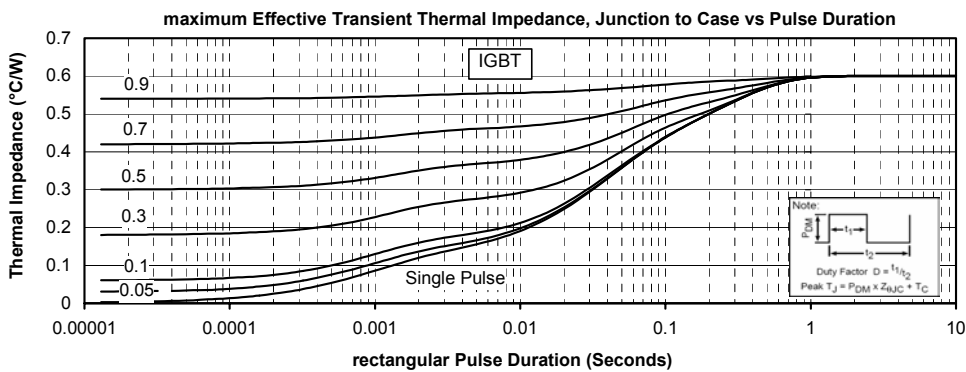
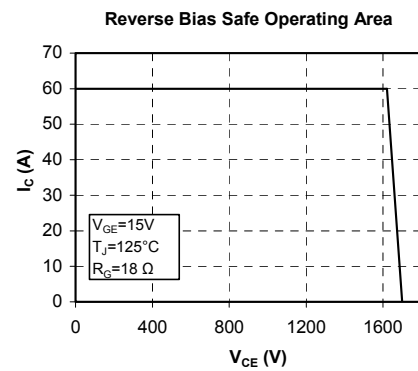
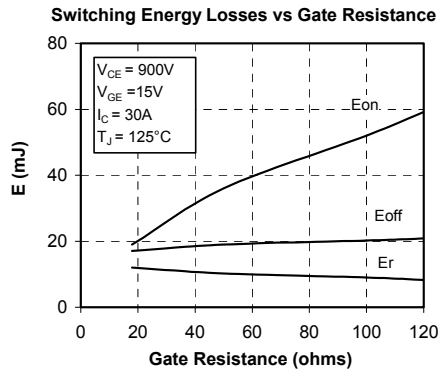
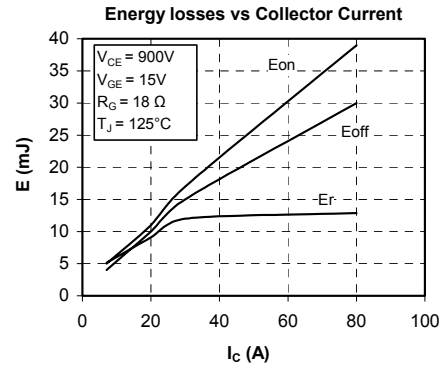
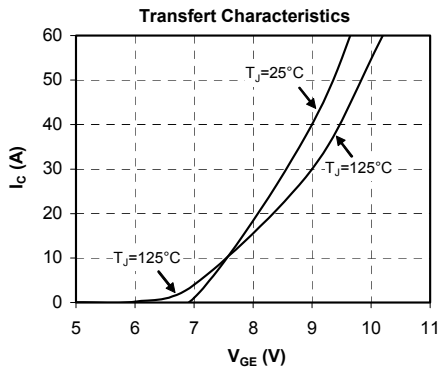
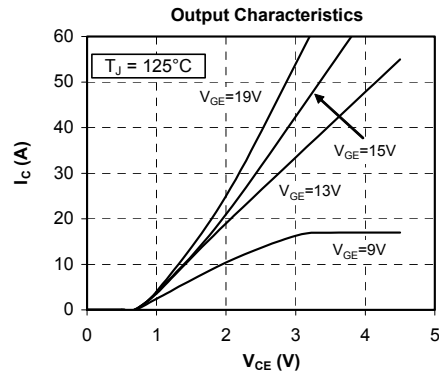
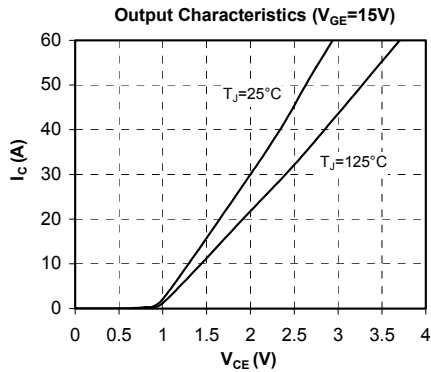
T: Thermistor temperature  
 R<sub>T</sub>: Thermistor value at T

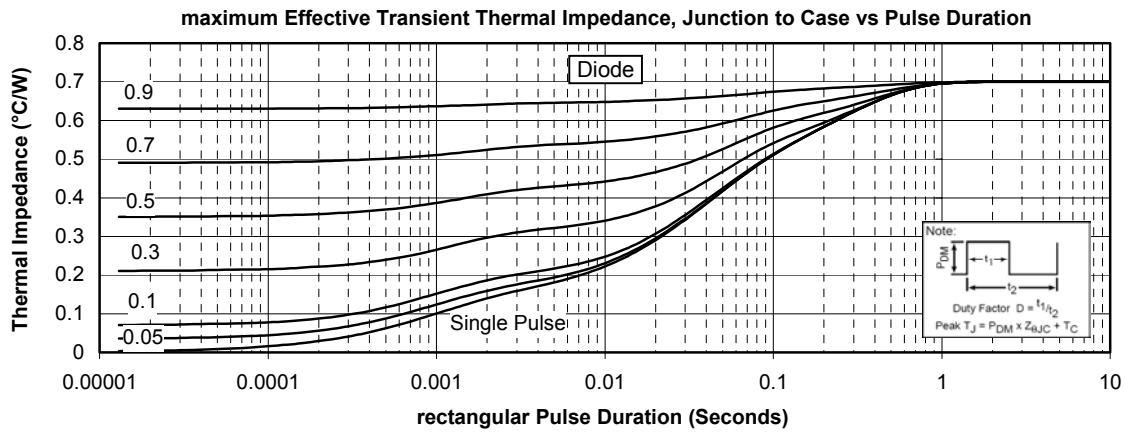
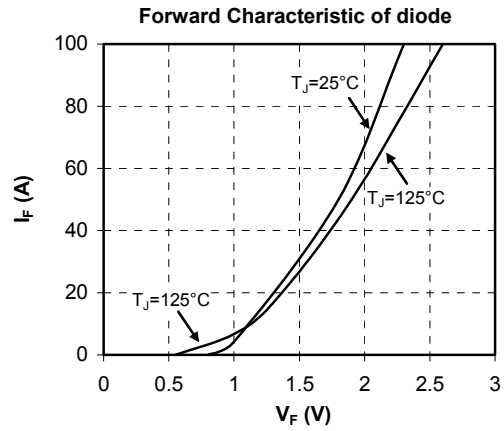
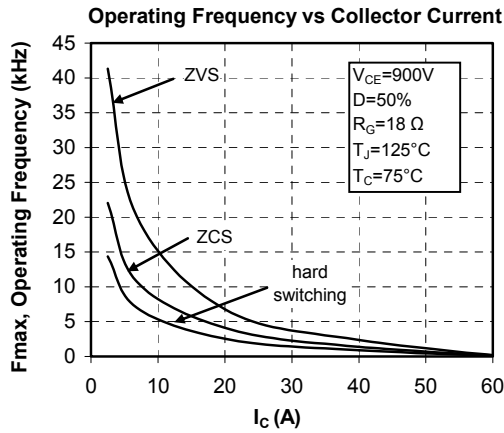
## SP1 Package outline (dimensions in mm)



See application note 1904 - Mounting Instructions for SP1 Power Modules on [www.microsemi.com](http://www.microsemi.com)

## Typical Performance Curve





Microsemi reserves the right to change, without notice, the specifications and information contained herein

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